

# CHONGQING CLOUDCHILD TECHNOLOGY CO., LTD

# **SOT-23 Plastic-Encapsulate MOSFETS**

# CC2310 N-Channel Power MOSFET

V <sub>DSS</sub>	R <sub>DS(ON)</sub> (Typ.)	I <sub>D</sub>
60.1/	70mΩ@10V	
60 V	82mΩ@4.5V	3A

# **DESCRIPTION**

The CC2310 provides excellent R<sub>DS(ON)</sub> with low gate charge.

It can be used in a wide variety of applications.

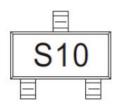
# **FEATURES**

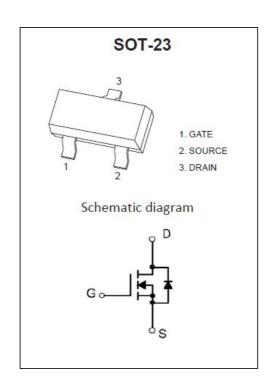
- High power and current handing capability
- Surface mount package
- AEC-Q101 Qualified

# **APPLICATIONS**

- Battery Switch
- DC/DC Converter

# **MARKING**





# ABSOLUTE MAXIMUM RATINGS(T<sub>j</sub>=25℃unless otherwise specified)

Parameter	Symbol	Value	Unit	
Drain - Source Voltage	V <sub>DS</sub>	60	V	
Gate - Source Voltage	V <sub>G</sub> s	±20	V	
Continuous Drain Current <sup>1,5</sup>	I <sub>D</sub> 3		А	
Pulsed Drain Current <sup>2</sup>	I <sub>DM</sub>	10	А	
Power Dissipation <sup>4,5</sup>	PD	1.8	W	
Thermal Resistance from Junction to Ambient <sup>5</sup>	R <sub>0</sub> JA	83.3	°C/W	
Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~ +175	$^{\circ}$ C

# MOSFET ELECTRICAL CHARACTERISTICS(TC=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Туре	Max	Unit
STATIC CHARACTERISTICS	'			•		
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> = 0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> = 0V			±100	nA
Gate Threshold Voltage <sup>3</sup>	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	1.2	2	V
Drain-Source On-Resistance <sup>3</sup>	В	V <sub>GS</sub> =10V, I <sub>D</sub> =3A		70	90	m0
	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A		82	123	mΩ
Forward Tranconductance <sup>3</sup>	<b>g</b> FS	V <sub>DS</sub> =15V, I <sub>D</sub> =2A	1.4	2.5		S
DYNAMIC CHARACTERISTICS						
Input Capacitance	C <sub>iss</sub>			250		
Output Capacitance	Coss	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V,f =1MHz		26		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			20		
SWITCHING CHARACTERISTICS						
Total Gate Charge	Qg			7		
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =4.5V,I <sub>D</sub> =3A		1.2		nC
Gate-Drain Charge	Q <sub>gd</sub>			1.5		
Turn-On Delay Time	t <sub>d(on)</sub>			6.5		
Turn-On Rise Time	t <sub>r</sub>	$V_{GS}$ =10V, $V_{DD}$ =30V, $I_{D}$ =1.5A, $R_{GEN}$ =1 $\Omega$		15.2		
Turn-Off Delay Time	t <sub>d(off)</sub>			15.2		ns
Turn-Off Fall Time	t <sub>f</sub>			10.3		
Source-Drain Diode characteristics	3					
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =3A,V <sub>GS</sub> =0V		0.8	1.2	V

Note:

1. The maximum current rating is limited by package.

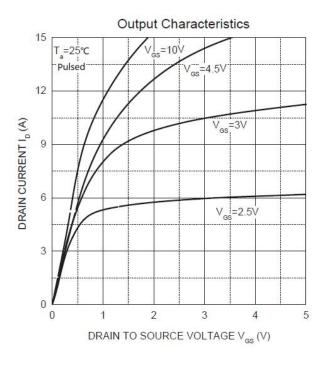
2. Pulse Test: Pulse Width ≤ 10μs, duty cycle ≤ 1%.

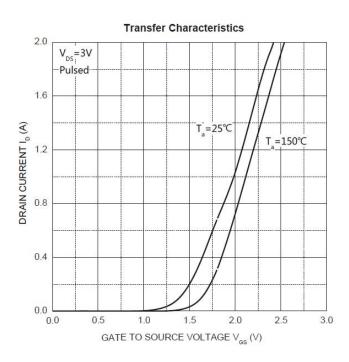
3. Pulse Test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.

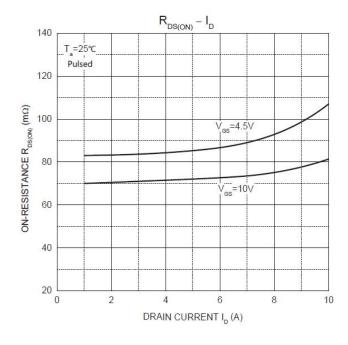
4. The power dissipation P<sub>D</sub> is limited by T<sub>J(MAX)</sub> = 175°C.

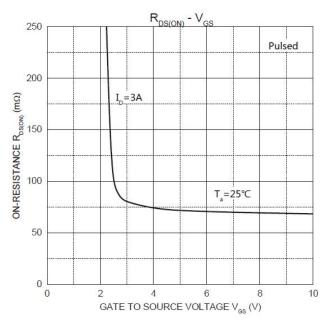
5. Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with TA =25°C.

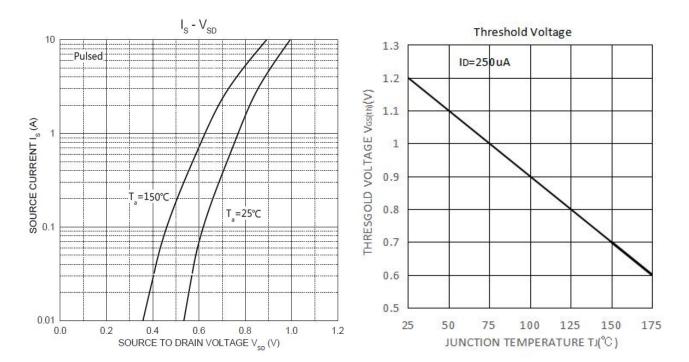
# **Characteristics Curve:**











# Maximum Forward Biased Safe Operating Area 10 Tc-25°C Single Pulse Raja-83.3°C/W 0.01ms 0.1ms 1ms



Vos(V)

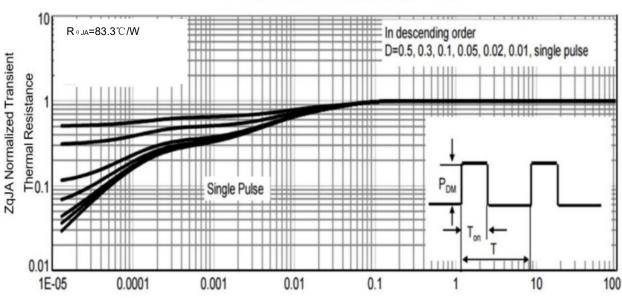
1

10

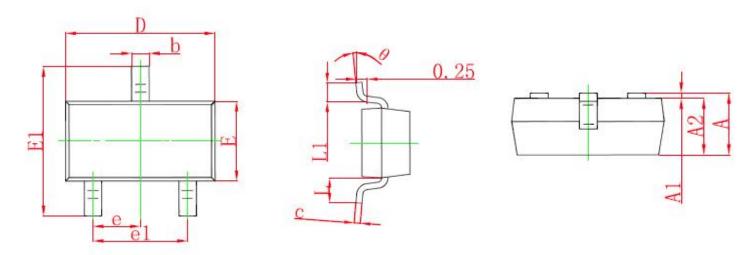
100

0.01

0.1



# **SOT-23 Package Outline Dimensions**



Cumbal	Dimensions	In Millimeters	Dimension	s in inches
Symbol	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950	TYP	0.037	TYP
e1	1.800	2.000	0.071	0.079
L	0.550	REF	0.022	REF
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

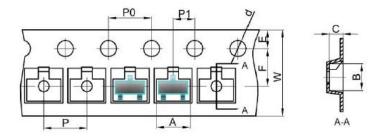
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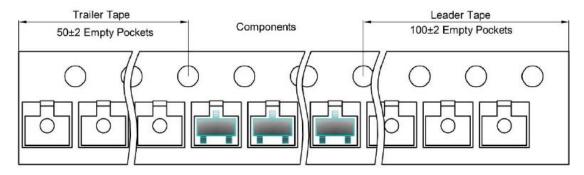
# SOT-23 Tape and reel

# SOT-23 Embossed Carrier Tape

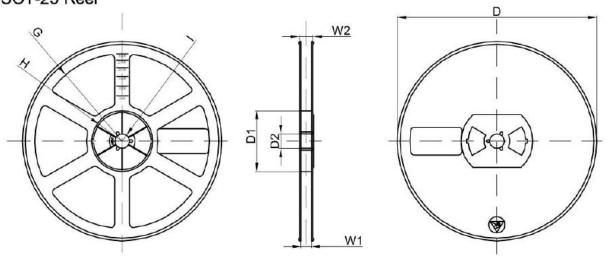


Dimensions are in millimeter										
Pkg type	Α	В	С	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

# SOT-23 Tape Leader and Trailer



# SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	Н	1	W1	W2
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	

Rev#	revise content
A/0	/